BTA206X-800CT



3Q Hi-Com Triac
Rev. 2 — 19 December 2011

Product data sheet

Product profile 1.

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series CT" triac will commutate the full RMS current at the maximum rated junction temperature ($T_i = 150 \, \text{°C}$) without the aid of a snubber. it is used where "high junction operating temperature capability" is required.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- Motor controls for home appliances
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5	-	-	60	Α
Tj	junction temperature		-	-	150	${\mathcal C}$
I _{T(RMS)}	RMS on-state current	full sine wave; T _h ≤ 114 °C; see Figure 1; see Figure 2: see Figure 3	-	-	6	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ C; see } \frac{\text{Figure 7}}{}$	4	-	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-; T_j = 25 \text{ °C;}$ see Figure 7	4	-	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G\text{-; } T_j = 25 \text{ °C; } see Figure 7$	4	-	35	mA
Dynamic c	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V $_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit	500	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 150 \text{ C}; I_{T(RMS)} = 6 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s}; \text{ (snubberless condition)}; \text{ gate open circuit}$	10	-	-	A/ms

2. Pinning information

Table 2. Pinning information

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Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		. .
2	T2	main terminal 2	mb	T2—T1
3	G	gate		`G sym051
mb	n.c.	mounting base; isolated		
			SOT186A (TO-220F)	

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BTA206X-800CT	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A		
BTA206X-800CT/L01	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 114 \text{°C}$; see Figure 1; see Figure 2; see Figure 3	-	6	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5	-	60	Α
		full sine wave; $T_{j(init)} = 25 \text{ C}$; $t_p = 16.7 \text{ ms}$	-	66	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	18	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 10 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	$\mathcal C$
T _j	junction temperature		-	150	$\mathcal C$

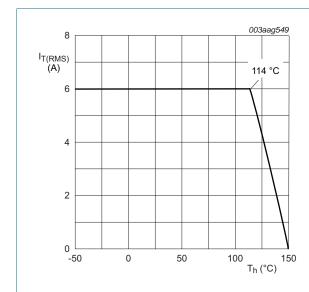
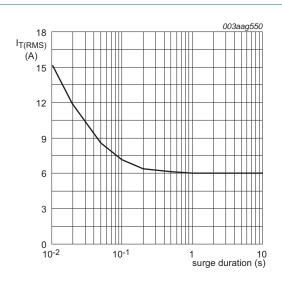


Fig 1. RMS on-state current as a function of heatsink temperature; maximum values



f = 50 Hz; T_h = 114 °C

Fig 2. RMS on-state current as a function of surge duration; maximum values

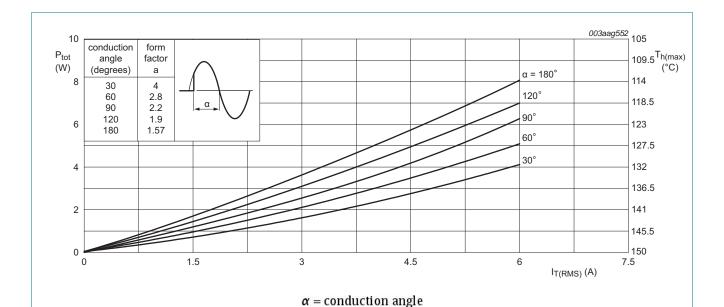


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

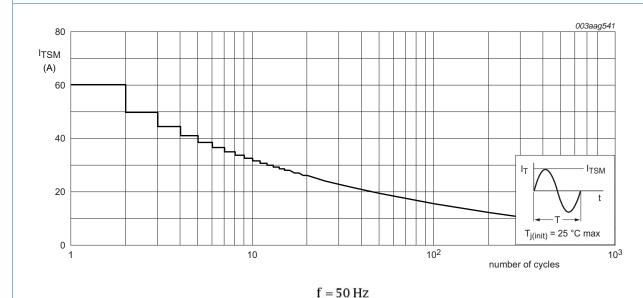
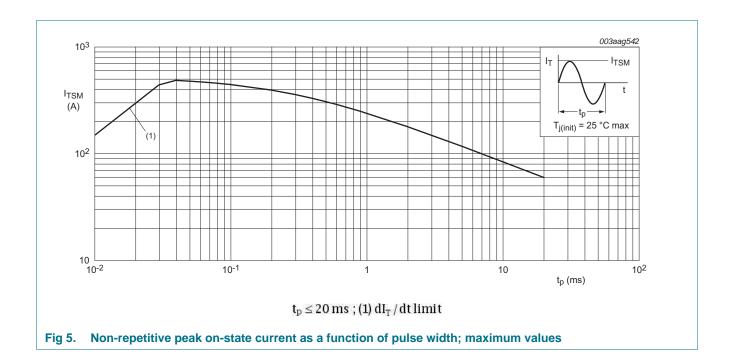


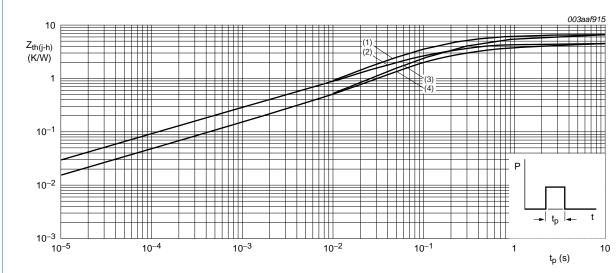
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; see Figure 6	-	-	4.5	K/W
		full cycle or half cycle; without heatsink compound; see Figure 6	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

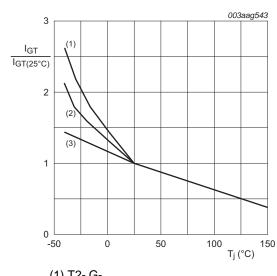
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 $^{\circ}$ C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink ; $f = 1 \text{ MHz}$; $T_h = 25 \text{C}$	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; see Figure 7	4	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 \text{ C};$ see <u>Figure 7</u>	4	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2\text{- G-}; T_j = 25 ^{\circ}\text{C};$ see Figure 7	4	-	35	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+; T_j = 25 \text{ C};$ see <u>Figure 8</u>	-	-	50	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-; T_j = 25 \text{ C};$ see <u>Figure 8</u>	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-}; T_j = 25 \text{ °C};$ see <u>Figure 8</u>	-	-	50	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 9}}{^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^{\circ}^$	-	-	35	mΑ
V_{T}	on-state voltage	I _T = 7 A; see <u>Figure 10</u>	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ C};$ see Figure 11	-	0.8	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 ^{\circ}\text{C}$	0.25	-	-	V
I _D	off-state current	$V_D = 800 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	0.4	2	mΑ
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V $_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit	500	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 150 \text{ C}; I_{T(RMS)} = 6 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s}; \text{ (snubberless condition)}; \text{ gate open circuit}$	10	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 150 \text{ C}; I_{T(RMS)} = 6 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s};$ gate open circuit	12	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 150 \text{ C}; I_{T(RMS)} = 6 \text{ A};$ $dV_{com}/dt = 1 \text{ V/}\mu\text{s}; \text{ gate open circuit}$	20	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig 7. Normalized gate trigger current as a function of junction temperature

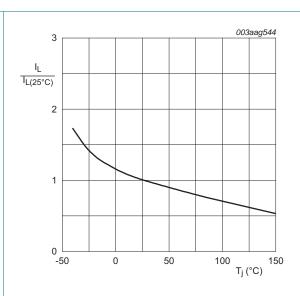
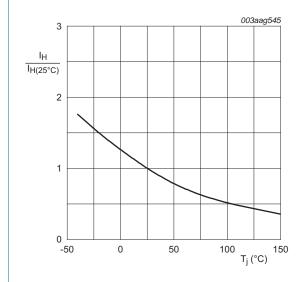
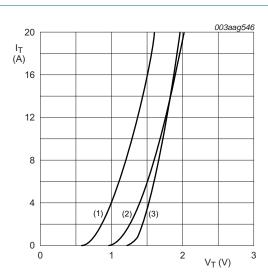


Fig 8. Normalized latching current as a function of junction temperature



Normalized holding current as a function of Fig 9. junction temperature



Vo = 1.184 V; Rs = 0.047 Ω

(1) Tj = 150 ℃; typical values

(2) Tj = 150 ℃; maximum values

(3) Tj = 25 ℃; maximum values

Fig 10. On-state current as a function of on-state voltage

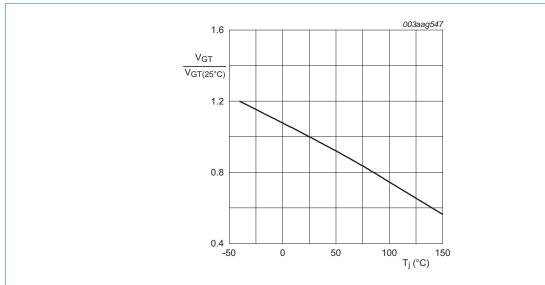
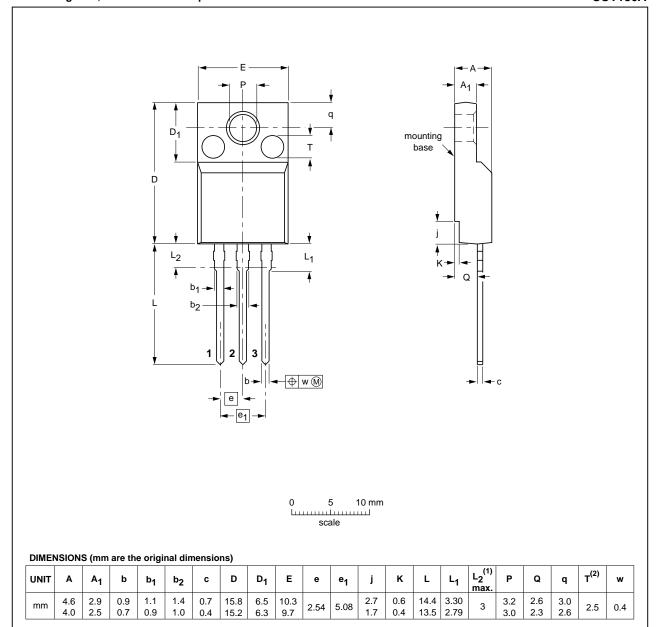


Fig 11. Normalized gate trigger voltage as a function of junction temperature

8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

	OUTLINE	REFERENCES				ISSUE DATE	
١ ٧	/ERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
,	SOT186A		3-lead TO-220F				-02-04-09 06-02-14

Fig 12. Package outline SOT186A (TO-220F)

BTA206X-800CT

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA206X-800CT v.2	20111219	Product data sheet	-	BTA206X-800CT v.1
Modifications:	 Various changes t 	o content.		
BTA206X-800CT v.1	20110823	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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